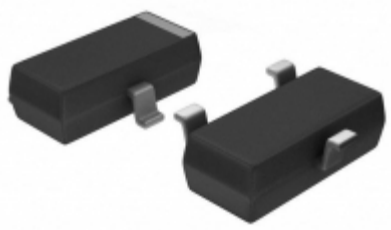

	<h2 style="color: #E67E22;">SI2311DS-T1-GE3</h2>
 <p style="font-size: small;">Image may be representation. See specs for product details.</p>	Hersteller-Teilenummer: SI2311DS-T1-GE3
	Hersteller / Marke: Electro-Films (EFI) / Vishay
	Teil der Beschreibung: MOSFET P-CH 8V 3A SOT23
	Datenblätter:  SI2311DS-T1-GE3.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 53206 pcs Stock Available.
Liefern von: Hong Kong	
Versandweg: DHL/Fedex/TNT/UPS/EMS	

Spezifikationen

Teilenummer	SI2311DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 8V 3A SOT23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	53206 pcs Stock
detaillierte Beschreibung	P-Channel 8V 3A (Ta) 710mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3
Verlustleistung (max)	710mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	8V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3A (Ta)
Rds On (Max) @ Id, Vgs	45 mOhm @ 3.5A, 4.5V
VGS (th) (Max) @ Id	800mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	12nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	970pF @ 4V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
























SI2311DS-T1-GE3 ist neu im Original, Suche SI2311DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2311DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2311DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2311DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 8V 3A SOT23</p>	 <p>SI2312-TP Micro Commercial Components (MCC) N-CHANNEL MOSFET, SOT-23 PACKAGE</p>	 <p>SI23120 VISHAY SI23120 VISHAY</p>	 <p>SI2311DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 8V 3A SOT23</p>
 <p>SI2311DS-T1 VISHAY SI2311DS-T1 VISHAY</p>	 <p>SI2311DS-T1-E3 Vishay / Siliconix MOSFET P-CH 8V 3A SOT23</p>	 <p>SI2312BDS VISHAY SI2312BDS VISHAY</p>	 <p>SI2312/CJ2312 Original SOT-23</p>

heiße Teile

Mehr

 SI2308BDS-T1-GE3	 SI2308BDS-T1-GE3	 SI2308DS	 SI2308DS-T1	 SI2308DS-T1-E3
 SI2308DS-T1-E3	 SI2308DS-T1-GE3	 SI2309BDS-T1-E3	 SI2309BDS-T1-GE3	 SI2309CDS-T1-GE3
 SI2309CDS-T1-GE3	 SI2309DS	 SI2309DS-T1	 SI2309DS-T1-E3	 SI2309DS-T1-E3
 SI2309DS-T1-GE3	 SI2309DS-TI-E3	 SI2309DS/A92T	 SI2310DS	 SI2310DS-T1-E3
 SI2310DS-T1-GE3	 SI2311DS	 SI2311DS-T1	 SI2311DS-T1-E3	 SI2311DS-T1-E3
 SI2311DS-T1-GE3	 SI2312BDS	 SI2312BDS-T1-E3	 SI2312BDS-T1-E3	 SI2312BDS-T1-GE3
 SI2312BDS-T1-GE3	 SI2312CDS-T1-E3	 SI2312CDS-T1-GE3	 SI2312CDS-T1-GE3	 SI2312DS
 SI2312DS-T1	 SI2312DS-T1-E3	 SI2312DS-T1-GE3	 SI2313DS	 SI2313DS-T1-E3
 SI2313DS-T1-GE3	 SI2314DS	 SI2314DS-T1-E3	 SI2314DS-T1-GE3	 SI2314EDS
 SI2314EDS-T1-E3	 SI2314EDS-T1-E3	 SI2314EDS-T1-GE3	 SI2314EDS-T1-GE3	 SI2315BDS

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited